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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Application Number	09/988,984	
			Filing Date	November 19, 2001	
			First Named Inventor	John T. Moore	
			Art Unit	2842 2823	
			Examiner Name	Not Yet Assigned	
Sheet	1	of	8	Attorney Docket Number	M4065.0608/P608.

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
TUP	AA	5,761,115	06/02/1998	Kozicki et al.	
TUP	AB	6,084,796	07/04/2000	Kozicki et al.	
TUP	AC	5,914,893	06/22/1999	Kozicki et al.	
TUP	AD	5,896,312	04/20/1999	Kozicki et al.	
TUP	AE	6,388,324	05/14/2002	Kozicki et al.	
TUP	AF	US 2002/0000666	01/03/2002	Kozicki et al.	
TUP	AG	5,500,532	03/19/1996	Kozicki et al.	
TUP	AH	6,418,049	07/09/2002	Kozicki et al.	
TUP	AI	5,751,012	05/12/1998	Wolstenholme et al.	
TUP	AJ	5,789,277	08/04/1998	Zahorik et al.	
TUP	AK	6,348,365	02/19/2202	Moore et al.	
	AL				
	AM				
	AN				
	AO				

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				
TUP	BA	WO 02/21542	03/14/2002	Kozicki et al.		
TUP	BB	WO 00/48196	08/17/2000	Kozicki et al.		
TUP	BC	WO 97/48032	12/18/1997	Kozicki et al.		
TUP	BD	WO 99/28914	06/10/1999	Kozicki et al.		

Examiner Signature	<i>John T. Moore</i>	Date Considered	3/20/03
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant

¹ Applicant's unique citation designation number (optional). ² See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

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Sheet 2 of 8

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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
Tup	CA	Abdel-Ail, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge ₅ As ₃₈ Te ₅₇ chalcogenide glass, Vacuum 59 (2000) 845-853.	
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Tup	CD	Afifi, M.A.; Labib, H.H.; El-Fazary, M.H.; Fadel, M., Electrical and thermal properties of chalcogenide glass system Se ₇₅ Ge ₂₅ -xSbx, Appl. Phys. A 55 (1992) 167-169.	
Tup	CE	Afifi, M.A.; Labib, H.H.; Fouad, S.S.; El-Shazly, A.A., Electrical & thermal conductivity of the amorphous semiconductor GexSe _{1-x} , Egypt, J. Phys. 17 (1986) 335-342.	
Tup	CF	Alekperova, Sh.M.; Gadzhieva, G.S., Current-Voltage characteristics of Ag ₂ Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139.	
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Tup	CH	Angell, C.A., Mobile ions in amorphous solids, Annu. Rev. Phys. Chem. 43 (1992) 693-717.	
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Tup	CL	Baranovskii, S.D.; Cordes, H., On the conduction mechanism in ionic glasses, J. Chem. Phys. 111 (1999) 7546-7557.	
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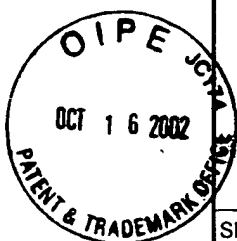
Sheet	3	of	8	Attorney Docket Number	M4065.0608/P608
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TUP	CY	Boolchand, P.; Georgiev, D.G.; Goodman, B., Discovery of the Intermediate Phase in Chalcogenide Glasses, J. Optoelectronics and Advanced Materials, 3 (2001), 703	
TUP	CZ	Boolchand, P.; Selvanathan, D.; Wang, Y.; Georgiev, D.G.; Bresser, W.J., Onset of rigidity in steps in chalcogenide glasses, Properties and Applications of Amorphous Materials, M.F. Thorpe and Tichy, L. (eds.) Kluwer Academic Publishers, the Netherlands, 2001, pp. 97-132.	
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Sheet	4	of	8
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Twp	CV1	silicon/nanodisperse metal (SIMAL) system-Films of unique electronic properties, J. Non-Cryst. Solids 198-200 (1996) 829-832.
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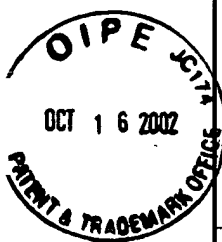
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Tup	CO3	Kawasaki, M.; Kawamura, J.; Nakamura, Y.; Aniya, M., Ionic conductivity of Ag _x (GeSe ₃) _{1-x} (0<=x<=0.571) glasses, Solid state Ionics 123 (1999) 259-269.
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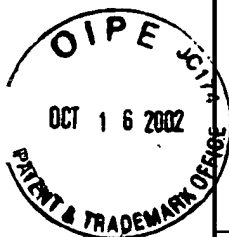
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Substitute for form 1449B/PTO		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	09/988,984
		Filing Date	November 19, 2001
		First Named Inventor	John T. Moore
		Group Art Unit	2012 28 23
		Examiner Name	Not Yet Assigned
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Sheet	8	of	8	Attorney Docket Number	M4065.0608/P608
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Application Number	09/988,984
Filing Date	November 19, 2001
First Named Inventor	John T. Moore
Group Art Unit	2842-2823
Examiner Name	Not Yet Assigned

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Examiner Signature	<i>Phan Thanh</i>	Date Considered	3/20/02
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				Application Number	09/988,984
				Filing Date	November 19, 2001
				First Named Inventor	John T. Moore
				Art Unit	2842 2823
				Examiner Name	Not Yet Assigned
Sheet	1	of	1	Attorney Docket Number	M4065.0608/P608

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
JP	AA	US 2002/0168820	11-14-2002	Kozicki, et al.	
JP	AB	6,469,364	10-22-2002	Kozicki	
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